

SEMICONDUCTOR

# **BC212B**

# **PNP General Purpose Amplifier**

- This device is designed for general purpose amplifier application at collector currents to 100mA.
- Sourced from process 68.



1. Collector 2. Base 3. Emitter

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# Absolute Maximum Ratings\* T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current - Continuous	100	mA	
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C	

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

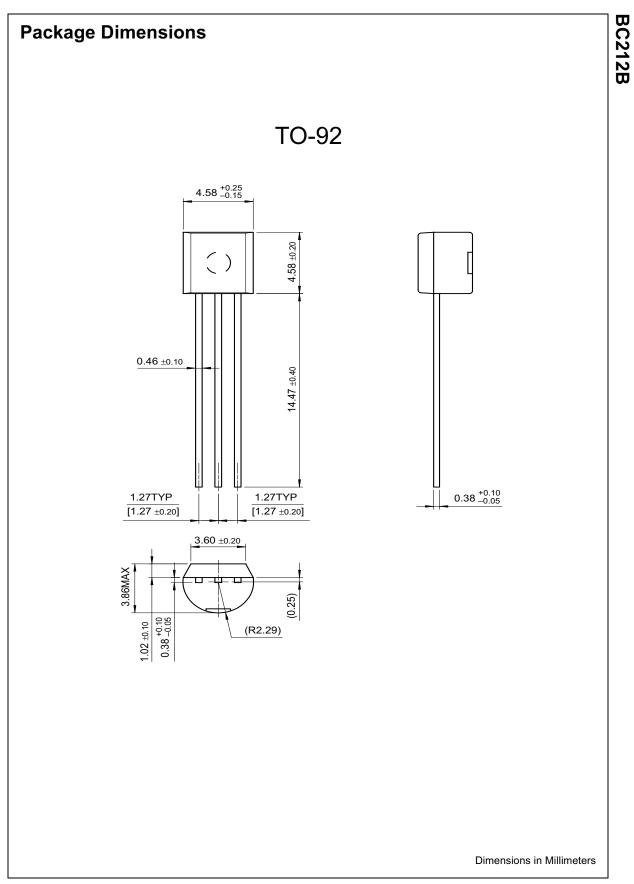
These ratings are based on a maximum junction temperature of 150°C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

## Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Chara	Off Characteristics					
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 2mA	50			V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10μA	60			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10μA	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 30V			15	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 4V			15	nA
On Chara	On Characteristics*					
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 10\mu A$ $V_{CE} = 5V, I_{C} = 2mA$	40 60			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA			0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA			1.4	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA	0.6		0.72	V
Small Signal Characteristics						
C <sub>ob</sub>	Output Capacitance	V <sub>CE</sub> = 10V, f = 1MHz			6	pF
h <sub>fe</sub>	Small Signal Current Gain	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA, f = 1KHz	200		400	
NF	Noise Figure	$V_{CE}$ = 5V, I <sub>C</sub> = 200µA, f = 1KHz R <sub>G</sub> = 2KΩ, BW = 200Hz			10	dB

\* Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

ol	Characteristics T <sub>A</sub> =25°C unless otherwise noted Parameter	Max.	Units
	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
	Thermal Resistance, Junction to Ambient	357	°C/W
	Thermal Resistance, Junction to Case	125	°C/W



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